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INFORMATION DISCLOSURE STATEMENT BY APPLICANT

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Sheet 1 of 1

Complete if Known

Application Number	10/026,462
Filing Date	December 27, 2002
First Named Inventor	Takeuchi et al.
Group Art Unit	1731
Examiner Name	TBA Sean Vincent
Attorney Docket Number	KOJIM-444

U.S. PATENT DOCUMENTS

Examiner Initials *	Cite No. ¹	U.S. Patent Document		Name of Patentee or Applicant of Cited Document	Date of Publication of Cited Document MM-DD-YYYY	Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear
		Number	Kind Code ² (if known)			
SV	A1	4,274,907	A	Vig et al.	06/23/81	
	A2	H532		Brandmayr	10/04/88	

FOREIGN PATENT DOCUMENTS

Examiner Initials *	Cite No. ¹	Foreign Patent Document			Name of Patentee or Applicant of Cited Document	Date of Publication of Cited Document MM-DD-YYYY	Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear	T ₆
		Office ³	Number ⁴	Kind Code ⁵ (if known)				
SV	B1	JP	11335140	A	Naoki	12/07/99		
	B2	JP	2000302482	A	Yasuhiro	10/31/00		

OTHER PRIOR ART -- NON PATENT LITERATURE DOCUMENTS

Examiner Initials *	Cite No. ¹	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date, page(s), volume-issue number(s), publisher, city and/or country where published.	T ²
SV		Takeuchi et al. "Properties of our developing next generation photomask substrate" Database accession No. 6584331, abstract. Photomask and X-Ray Mask technology VI, Yokohama, Japan, 13-14, April 1999, Vol. 3748, pp. 41-52.	
		Patent Abstracts of Japan, Vol. 2000, No. 03, March 30, 2000, abstract.	
		Patent Abstracts of Japan, Vol. 2000, No. 13, 02/06/01, abstract.	
SV		Phase Shift Mask Fabrication Using Reactive Ion Etching of Quartz Substrates" Research Disclosure, Kenneth Mason Publications, Hampshire, GB, No. 340, August 1, 1992, page 682, abstract	
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